

Abstracts

Wideband High Gain Small Size Monolithic GaAs FET Amplifiers (1983 [MWSYM])

V. Pauker and M. Binet. "Wideband High Gain Small Size Monolithic GaAs FET Amplifiers (1983 [MWSYM])." 1983 MTT-S International Microwave Symposium Digest 83.1 (1983 [MWSYM]): 50-53.

A series of two to four stage monolithic amplifiers operating with a gain of 15 to 42 dB and covering the 0.1 to 2 till 4 GHz frequency band has been realized. A high density of integration has been achieved (active area of 0.2 mm²) as no decoupling capacitors nor inductance have been used.

 [Return to main document.](#)